

EFC8811R

Advance Information Power MOSFET 12V, 3.2mΩ, 27A, Dual N-Channel

This Power MOSFET features a low on-state resistance. This device is suitable for applications such as power switches of portable machines. Best suited for single cell lithium-ion battery applications.

Features

- 2.5V drive
- 2kV ESD HBM
- Common-Drain Type
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS compliance

Applications

- Single Cell Lithium-ion Battery Charging and Discharging Switch

SPECIFICATIONS

ABSOLUTE MAXIMUM RATINGS at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Source to Source Voltage	V _{SS}	12	V
Gate to Source Voltage	V _{GSS}	±8	V
Source Current (DC)	I _S	27	A
Source Current (Pulse) PW≤100μs, duty cycle≤1%	I _{SP}	100	A
Total Dissipation When mounted on ceramic substrate (5000mm ² × 0.8mm)	P _T	2.5	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (5000mm ² × 0.8mm)	R _{θJA}	50	°C/W

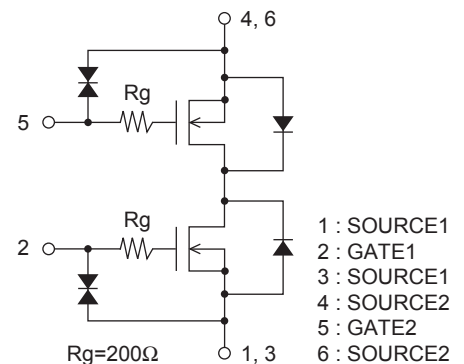


ON Semiconductor®

www.onsemi.com

V _{SS}	R _{SS(on)} Max	I _S Max
12V	3.2mΩ@ 4.5V	27A
	3.2mΩ@ 4.0V	
	3.2mΩ@ 3.8V	
	4.4mΩ@ 3.1V	
	6.3mΩ@ 2.5V	

ELECTRICAL CONNECTION N-Channel



CSP6, 1.77x3.54 /
EFCP3517-6DGH-020

MARKING



ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

This document contains information on a new product. Specifications and information herein are subject to change without notice.

EFC8811R

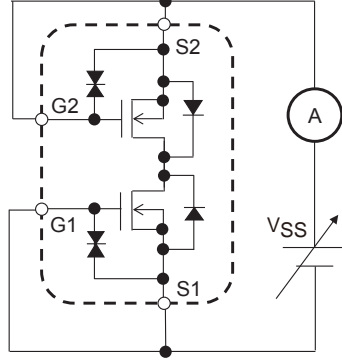
ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 2)

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Source to Source Breakdown Voltage	V(BR)SSS	I _S =1mA, V _{GS} =0V Test Circuit 1	12			V
Zero-Gate Voltage Source Current	I _{SSS}	V _{SS} =10V, V _{GS} =0V Test Circuit 1			1	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{SS} =0V Test Circuit 2			±1	μA
Gate Threshold Voltage	V _{GS(th)}	V _{SS} =6V, I _S =1mA Test Circuit 3	0.5		1.3	V
Forward Transconductance	g _{FS}	V _{SS} =6V, I _S =3A Test Circuit 4		19		S
Static Source to Source On-State Resistance	R _{SS(on)1}	I _S =5A, V _{GS} =4.5V Test Circuit 5	1.8	2.3	3.2	mΩ
	R _{SS(on)2}	I _S =5A, V _{GS} =4.0V Test Circuit 5	1.9	2.4	3.2	mΩ
	R _{SS(on)3}	I _S =5A, V _{GS} =3.8V Test Circuit 5	2.0	2.6	3.2	mΩ
	R _{SS(on)4}	I _S =5A, V _{GS} =3.1V Test Circuit 5	2.1	3.3	4.4	mΩ
	R _{SS(on)5}	I _S =5A, V _{GS} =2.5V Test Circuit 5	2.7	4.0	6.3	mΩ
Turn-ON Delay Time	t _{d(on)}	V _{SS} =6V, V _{GS} =4.5V, I _S =3A Test Circuit 6		80		ns
Rise Time	t _r			570		ns
Turn-OFF Delay Time	t _{d(off)}			38,000		ns
Fall Time	t _f			17,700		ns
Total Gate Charge	Q _g		V _{SS} =6V, V _{GS} =4.5V, I _S =27A Test Circuit 7		100	
Forward Source to Source Voltage	V _{F(S-S)}	I _S =3A, V _{GS} =0V Test Circuit 8		0.75	1.2	V

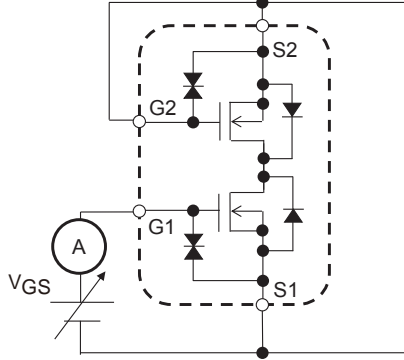
Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Test circuits are example of measuring FET1 side

Test Circuit 1
V_{SSS} / I_{SSS}

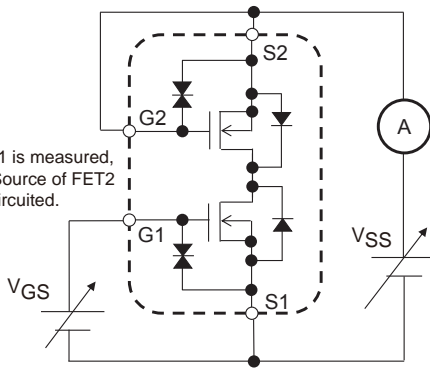


Test Circuit 2
I_{GSS}



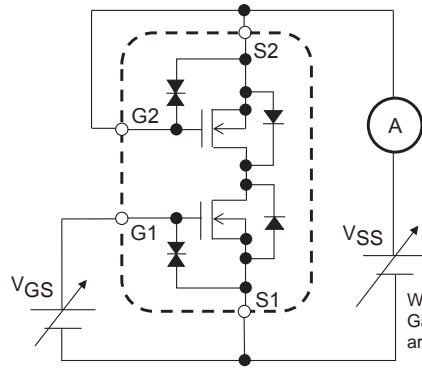
When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 3
V_{GS(th)}



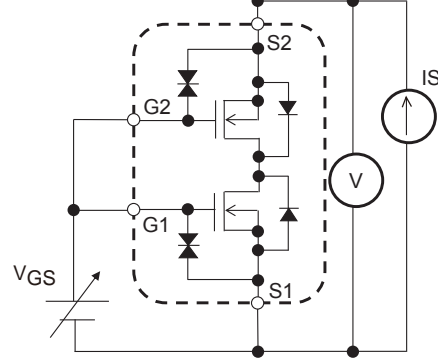
When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 4
g_{FS}

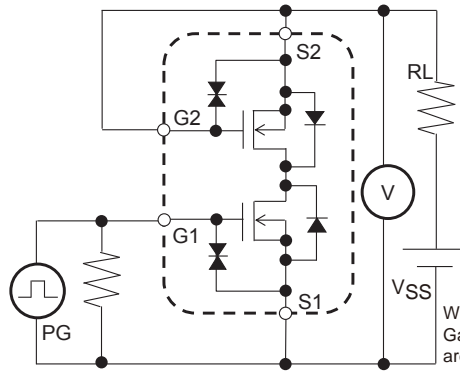


When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 5
R_{SS(on)}

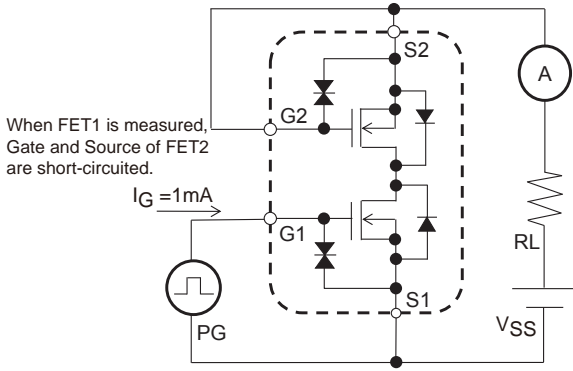


Test Circuit 6
t_{d(on)}, t_r, t_{d(off)}, t_f



When FET1 is measured, Gate and Source of FET2 are short-circuited.

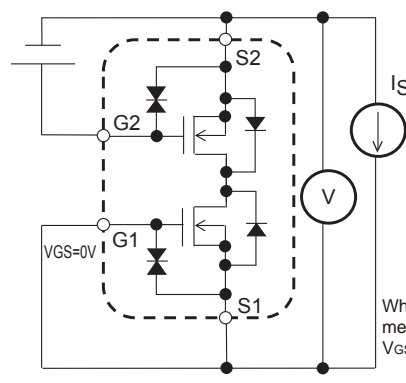
Test Circuit 7
Q_g



When FET1 is measured, Gate and Source of FET2 are short-circuited.

I_G = 1mA

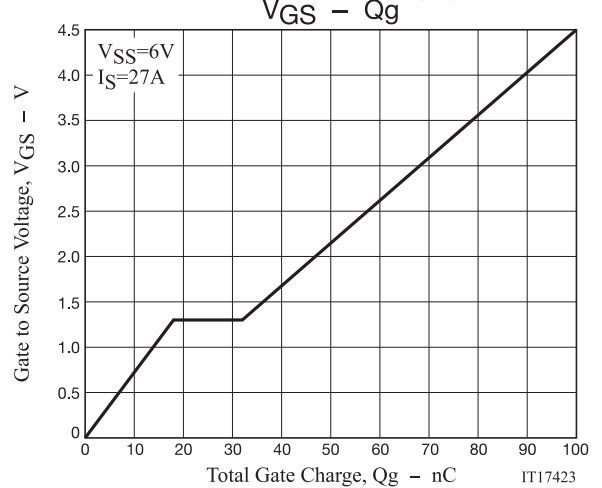
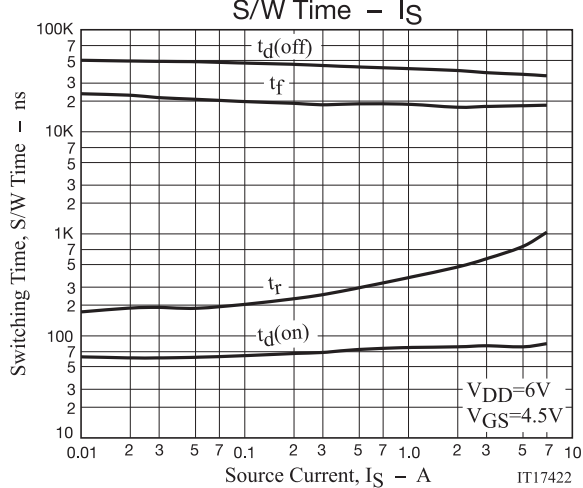
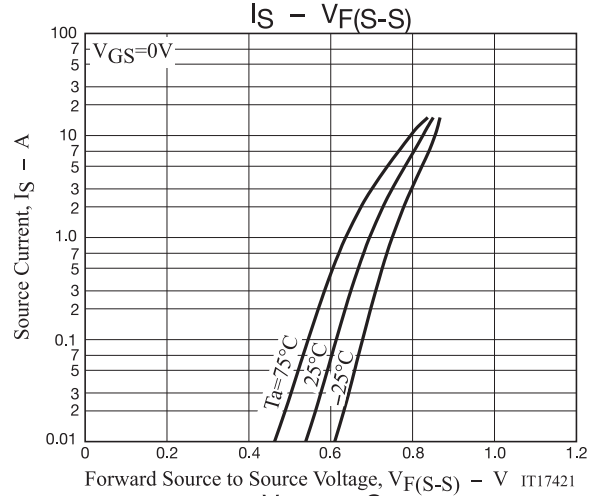
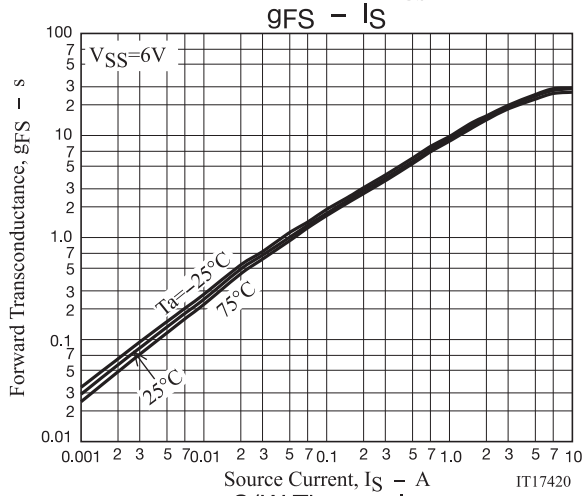
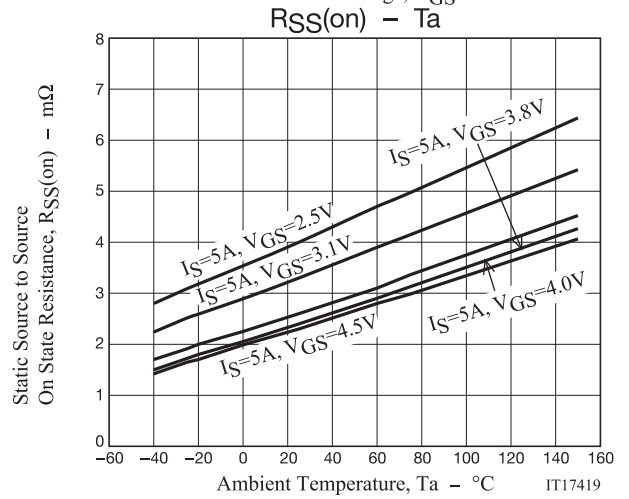
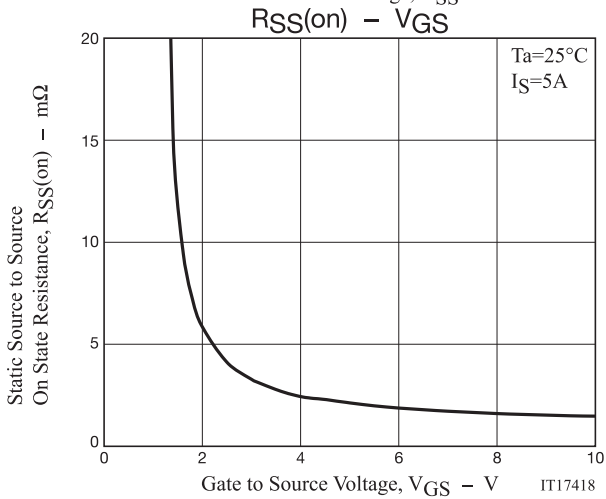
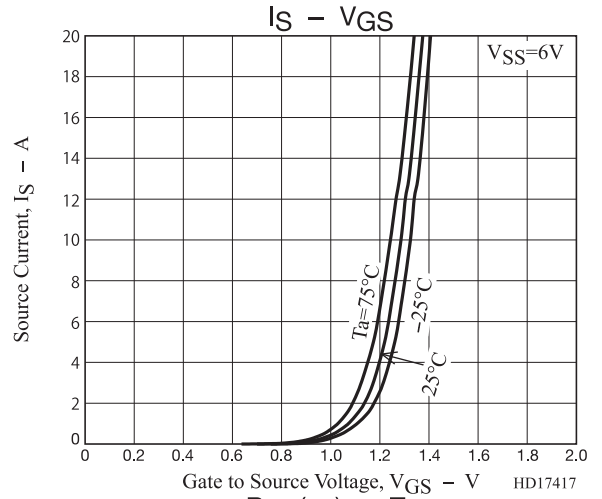
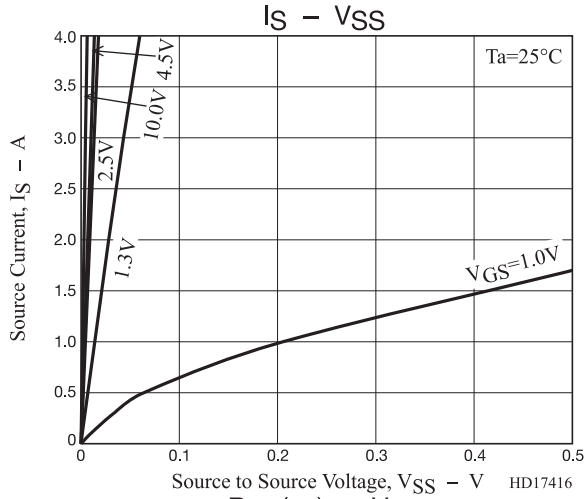
Test Circuit 8
V_{F(S-S)}



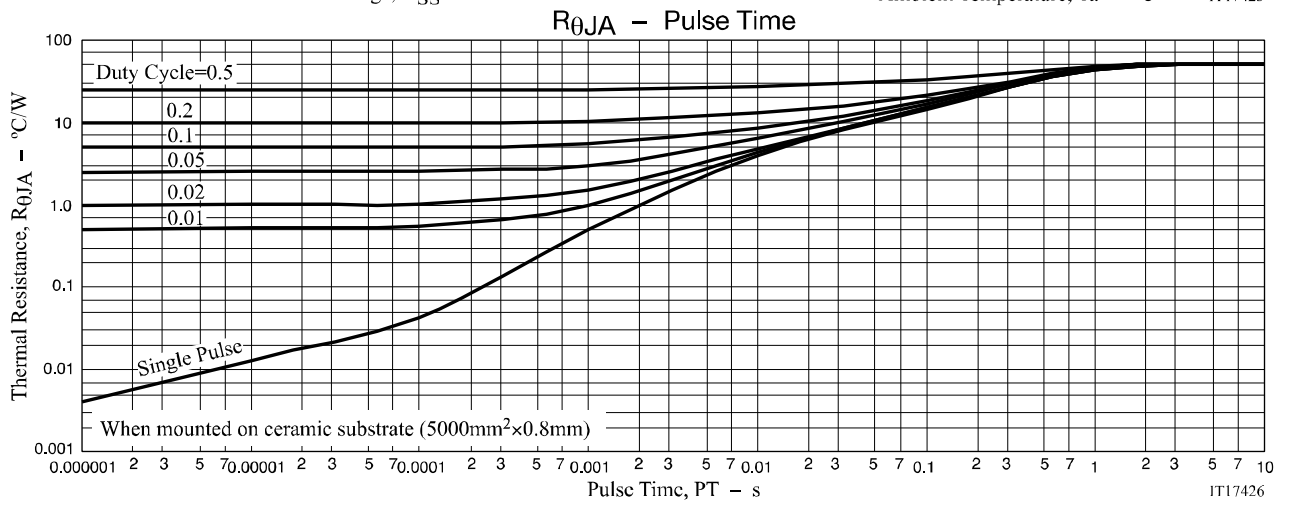
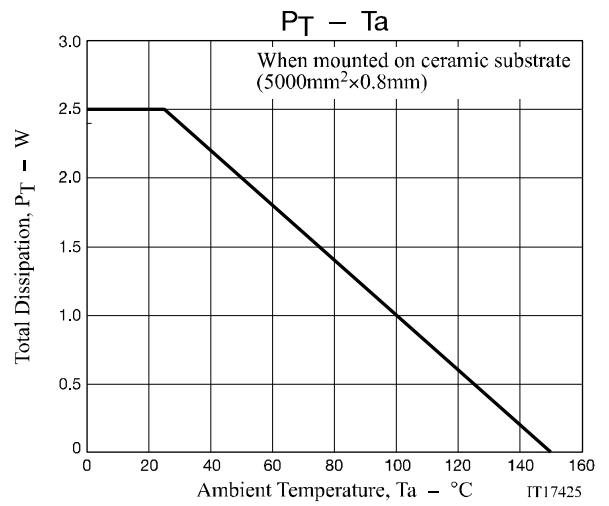
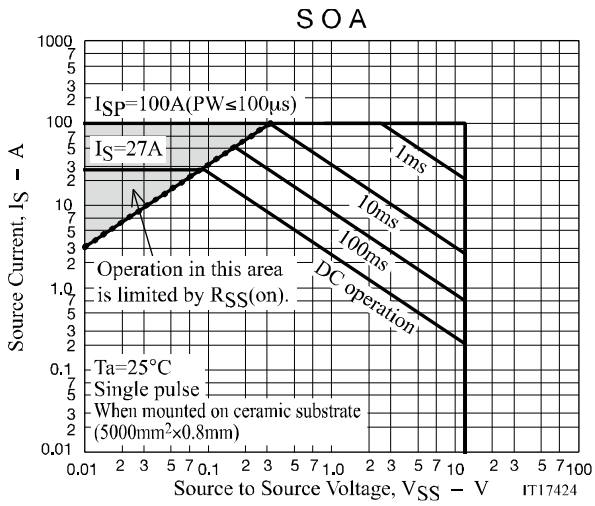
When FET1 is measured, +4.5V is added to V_{GS} of FET2.

When FET2 is measured, the position of FET1 and FET2 is switched.

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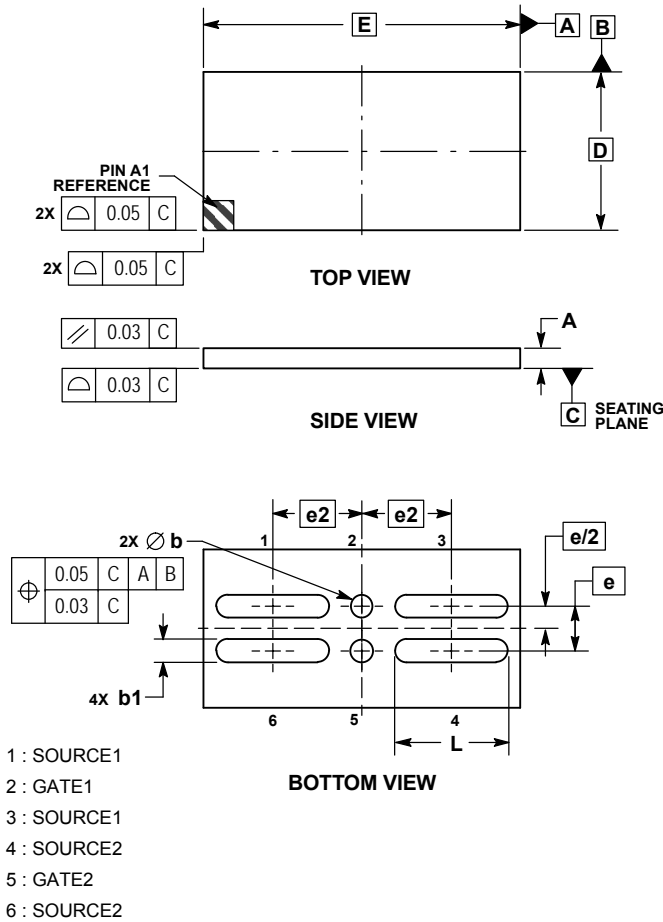
PACKAGE DIMENSIONS

unit : mm

CSP6, 1.77x3.54 / EFCP3517-6DGH-020

CASE 568AL

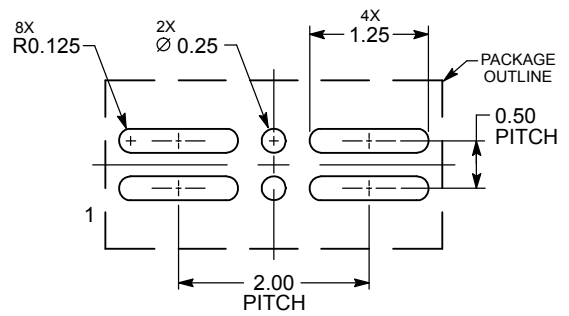
ISSUE O



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.

DIM	MILLIMETERS	
	MIN	MAX
A	---	0.22
b	0.22	0.28
b1	0.22	0.28
D	1.77 BSC	
E	3.54 BSC	
e	0.50 BSC	
e2	1.00 BSC	
L	1.22	1.28

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)
EFC8811R-TF	ML	CSP6, 1.77x3.54 / EFCP3517-6DGH-020 (Pb-Free / Halogen Free)	5,000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage : Since the EFC8811R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects. Please contact us for use except the designated application.

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